

Complementary N- and P-Channel 20 V (D-S) MOSFET

| PRODUCT SUMMARY | | | | |
|-----------------|---------------------|-----------------------------------|--------------------|-----------------------|
| | V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) | Q _g (TYP.) |
| N-Channel | 20 | 0.396 at V _{GS} = 4.5 V | 0.50 | 0.75 nC |
| | | 0.456 at V _{GS} = 2.5 V | 0.20 | |
| | | 0.546 at V _{GS} = 1.8 V | 0.20 | |
| | | 0.760 at V _{GS} = 1.5 V | 0.05 | |
| P-Channel | -20 | 0.756 at V _{GS} = -4.5 V | -0.35 | 1 nC |
| | | 1.038 at V _{GS} = -2.5 V | -0.35 | |
| | | 1.440 at V _{GS} = -1.8 V | -0.10 | |
| | | 2.400 at V _{GS} = -1.5 V | -0.05 | |

FEATURES

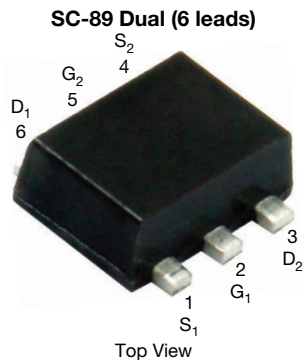
- TrenchFET® power MOSFETs
- High-side switching
- Ease in driving switches
- Low offset (error) voltage
- Low-voltage operation
- High-speed circuits
- Typical ESD protection:
n-channel 900 V, p-channel 900 V (HBM)
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

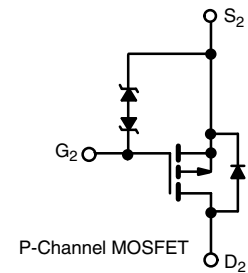
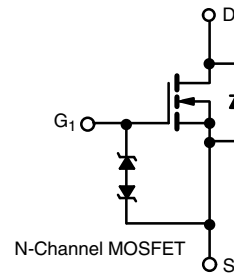
- Load switch, small signal switches and level-shift switches
 - Battery operated systems
 - Portable



Marking Code: 5

Ordering Information:

Si1016CX-T1-GE3 (Lead (Pb)-free and Halogen-free)



| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | | |
|---|-----------------------------------|------------------------|------------|------------|-----------|
| PARAMETER | SYMBOL | N-CHANNEL | P-CHANNEL | UNIT | |
| Drain-Source Voltage | V _{DS} | 20 | -20 | V | |
| Gate-Source Voltage | V _{GS} | ± 8 | | | |
| Continuous Drain Current (T _J = 150 °C) | I _D | T _A = 25 °C | 0.6 a, b | -0.6 a, b | |
| | | T _A = 70 °C | 0.49 a, b | -0.49 a, b | |
| Pulsed Drain Current (t = 300 μs) | I _{DM} | 2 | -1.5 | A | |
| Source Drain Current Diode Current | I _S | 0.18 a, b | -0.18 a, b | W | |
| Maximum Power Dissipation | P _D | T _A = 25 °C | 0.22 a, b | | 0.22 a, b |
| | | T _A = 70 °C | 0.14 a, b | | 0.14 a, b |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | -55 to 150 | | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------------|--------------|-----------|------|-----------|------|------|
| PARAMETER | SYMBOL | N-CHANNEL | | P-CHANNEL | | UNIT |
| | | TYP. | MAX. | TYP. | MAX. | |
| Maximum Junction-to-Ambient a, c | t ≤ 5 s | 470 | 565 | 470 | 565 | °C/W |
| | Steady State | 560 | 675 | 560 | 675 | |

Notes

- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 675 °C/W.



| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | | |
|---|--------------------------------------|---|------|------|-------|-------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | N-Ch | 20 | - | - | V |
| | | V _{GS} = 0 V, I _D = -250 μA | P-Ch | -20 | - | - | |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = 250 μA | N-Ch | - | 17 | - | mV/°C |
| | | I _D = -250 μA | P-Ch | - | -12 | - | |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | I _D = 250 μA | N-Ch | - | -1.8 | - | mV/°C |
| | | I _D = -250 μA | P-Ch | - | 1.8 | - | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | N-Ch | 0.4 | - | 1 | V |
| | | V _{DS} = V _{GS} , I _D = -250 μA | P-Ch | -0.4 | - | -1 | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 4.5 V | N-Ch | - | - | ± 1 | μA |
| | | | P-Ch | - | - | ± 1 | |
| | | V _{DS} = 0 V, V _{GS} = ± 8 V | N-Ch | - | - | ± 30 | |
| | | | P-Ch | - | - | ± 30 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 20 V, V _{GS} = 0 V | N-Ch | - | - | 1 | μA |
| | | V _{DS} = -20 V, V _{GS} = 0 V | P-Ch | - | - | -1 | |
| | | V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C | N-Ch | - | - | 10 | |
| | | V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C | P-Ch | - | - | -10 | |
| On-State Drain Current ^b | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 4.5 V | N-Ch | 2 | - | - | A |
| | | V _{DS} ≤ -5 V, V _{GS} = -4.5 V | P-Ch | -1.5 | - | - | |
| Drain-Source On-State Resistance ^b | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 0.5 A | N-Ch | - | 0.330 | 0.396 | Ω |
| | | V _{GS} = -4.5 V, I _D = -0.35 A | P-Ch | - | 0.630 | 0.756 | |
| | | V _{GS} = 2.5 V, I _D = 0.2 A | N-Ch | - | 0.380 | 0.456 | |
| | | V _{GS} = -2.5 V, I _D = -0.35 A | P-Ch | - | 0.865 | 1.038 | |
| | | V _{GS} = 1.8 V, I _D = 0.2 A | N-Ch | - | 0.420 | 0.546 | |
| | | V _{GS} = -1.8 V, I _D = -0.1 A | P-Ch | - | 1.200 | 1.440 | |
| | | V _{GS} = 1.5 V, I _D = 0.05 A | N-Ch | - | 0.505 | 0.760 | |
| Forward Transconductance ^b | g _{fs} | V _{DS} = 10 V, I _D = 0.5 A | N-Ch | - | 2 | - | S |
| | | V _{DS} = -10 V, I _D = -3.6 A | P-Ch | - | 1 | - | |
| Input Capacitance | C _{iss} | N-Channel V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | N-Ch | - | 43 | - | pF |
| Output Capacitance | C _{oss} | | P-Ch | - | 45 | - | |
| Reverse Transfer Capacitance | C _{rss} | P-Channel V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz | N-Ch | - | 14 | - | |
| | | | P-Ch | - | 15 | - | |
| Dynamic ^a | | | | | | | |
| Total Gate Charge | Q _g | V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 0.6 A | N-Ch | - | 1.3 | 2 | nC |
| | | V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -0.4 A | P-Ch | - | 1.65 | 2.50 | |
| Gate-Source Charge | Q _{gs} | N-Channel V _{DS} = 10 V, V _{GS} = 2.5 V, I _D = 0.6 A | N-Ch | - | 0.75 | 1.2 | |
| | | | P-Ch | - | 1 | 2 | |
| Gate-Drain Charge | Q _{gd} | P-Channel V _{DS} = -10 V, V _{GS} = -2.5 V, I _D = -0.4 A | N-Ch | - | 0.15 | - | |
| | | | P-Ch | - | 0.2 | - | |
| Gate Resistance | R _g | f = 1 MHz | N-Ch | 2.4 | 12.2 | 24.4 | Ω |
| | | | P-Ch | 2.4 | 12 | 24 | |



| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | | |
|---|---------------------|---|------|------|-------|------|----|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
| Dynamic ^a | | | | | | | |
| Turn-On Delay Time | t _{d(on)} | N-Channel V _{DD} = 10 V, R _L = 20 Ω I _D ≅ 0.5 A, V _{GEN} = 4.5 V, R _g = 1 Ω | N-Ch | - | 11 | 20 | ns |
| | | | P-Ch | - | 9 | 18 | |
| Rise Time | t _r | P-Channel V _{DD} = -10 V, R _L = 33.3 Ω I _D ≅ -0.3 A, V _{GEN} = -4.5 V, R _g = 1 Ω | N-Ch | - | 16 | 24 | |
| | | | P-Ch | - | 10 | 20 | |
| Turn-Off Delay Time | t _{d(off)} | N-Channel V _{DD} = 10 V, R _L = 20 Ω I _D ≅ 0.5 A, V _{GEN} = 8 V, R _g = 1 Ω | N-Ch | - | 26 | 39 | |
| | | | P-Ch | - | 10 | 20 | |
| Fall Time | t _f | P-Channel V _{DD} = -10 V, R _L = 33.3 Ω I _D ≅ -0.3 A, V _{GEN} = -8 V, R _g = 1 Ω | N-Ch | - | 11 | 20 | |
| | | | P-Ch | - | 8 | 16 | |
| Turn-On Delay Time | t _{d(on)} | N-Channel V _{DD} = 10 V, R _L = 20 Ω I _D ≅ 0.5 A, V _{GEN} = 8 V, R _g = 1 Ω | N-Ch | - | 2 | 4 | |
| | | | P-Ch | - | 1 | 2 | |
| Rise Time | t _r | P-Channel V _{DD} = -10 V, R _L = 33.3 Ω I _D ≅ -0.3 A, V _{GEN} = -8 V, R _g = 1 Ω | N-Ch | - | 13 | 20 | |
| | | | P-Ch | - | 8 | 16 | |
| Turn-Off Delay Time | t _{d(off)} | N-Channel V _{DD} = 10 V, R _L = 20 Ω I _D ≅ 0.5 A, V _{GEN} = 8 V, R _g = 1 Ω | N-Ch | - | 7 | 14 | |
| | | | P-Ch | - | 9 | 18 | |
| Fall Time | t _f | P-Channel V _{DD} = -10 V, R _L = 33.3 Ω I _D ≅ -0.3 A, V _{GEN} = -8 V, R _g = 1 Ω | N-Ch | - | 5 | 10 | |
| | | | P-Ch | - | 5 | 10 | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Pulse Diode Forward Current ^a | I _{SM} | I _S = 0.5 A, V _{GS} = 0 V | N-Ch | - | - | 2 | A |
| | | | P-Ch | - | - | -1.5 | |
| Body Diode Voltage | V _{SD} | I _S = 0.5 A, V _{GS} = 0 V | N-Ch | - | 0.85 | 1.2 | V |
| | | I _S = -0.3 A, V _{GS} = 0 V | P-Ch | - | -0.87 | -1.2 | |
| Body Diode Reverse Recovery Time | t _{rr} | N-Channel I _F = 0.5 A, di/dt = 100 A/μs, T _J = 25 °C | N-Ch | - | 10 | 20 | ns |
| | | | P-Ch | - | 16 | 24 | |
| Body Diode Reverse Recovery Charge | Q _{rr} | P-Channel I _F = -0.3 A, di/dt = -100 A/μs, T _J = 25 °C | N-Ch | - | 2 | 4 | nC |
| | | | P-Ch | - | 8 | 20 | |
| Reverse Recovery Fall Time | t _a | N-Channel I _F = 0.5 A, di/dt = 100 A/μs, T _J = 25 °C | N-Ch | - | 5 | - | ns |
| | | | P-Ch | - | 11 | - | |
| Reverse Recovery Rise Time | t _b | P-Channel I _F = -0.3 A, di/dt = -100 A/μs, T _J = 25 °C | N-Ch | - | 5 | - | |
| | | | P-Ch | - | 5 | - | |

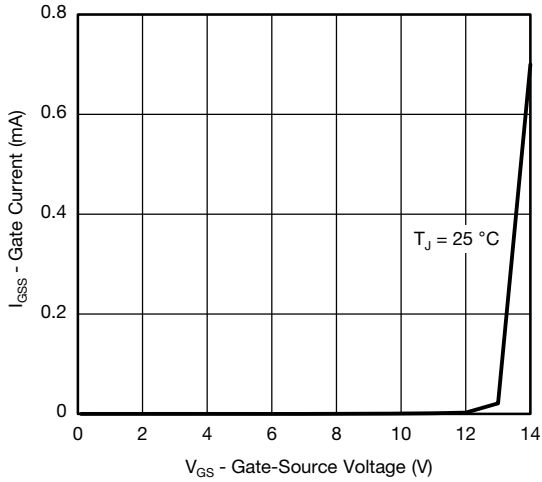
Notes

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.

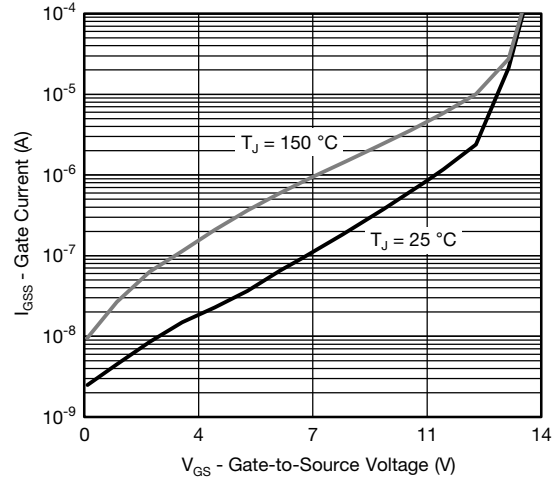
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



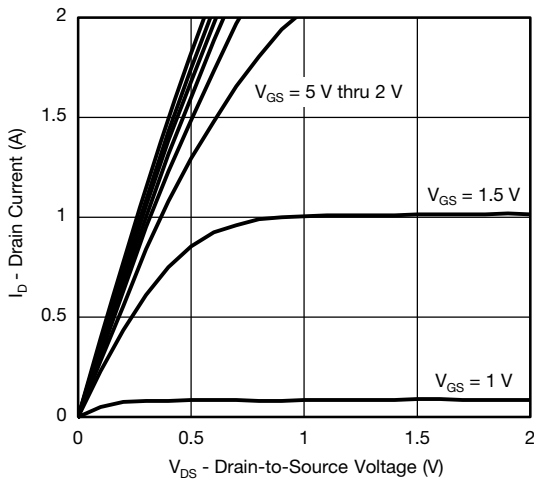
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



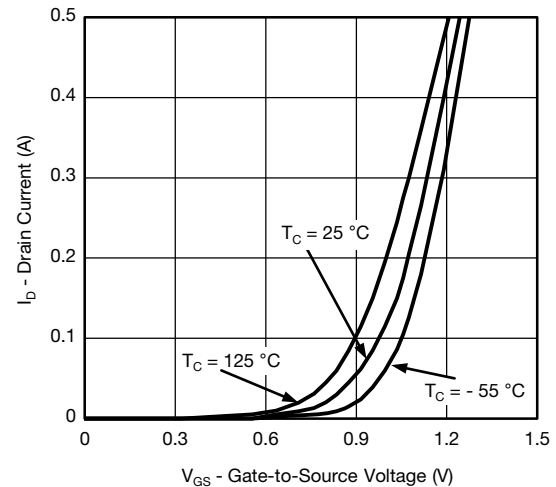
Gate Current vs. Gate-Source Voltage



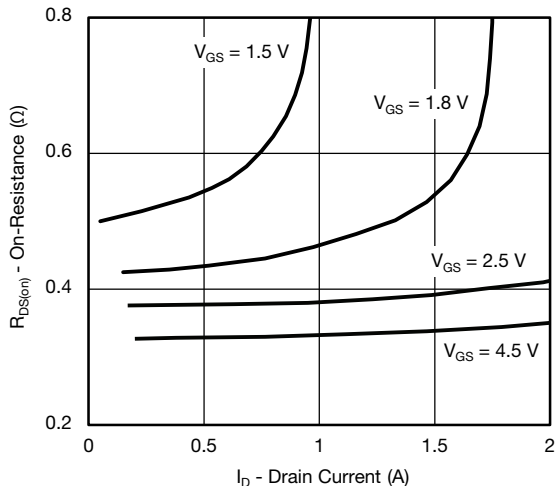
Gate Current vs. Gate-Source Voltage



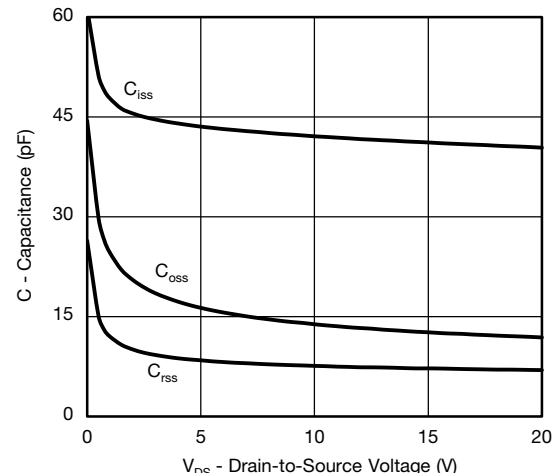
Output Characteristics



Transfer Characteristics

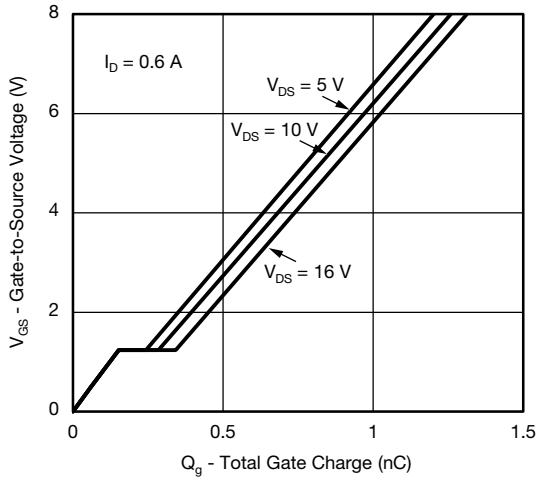


On-Resistance vs. Drain Current

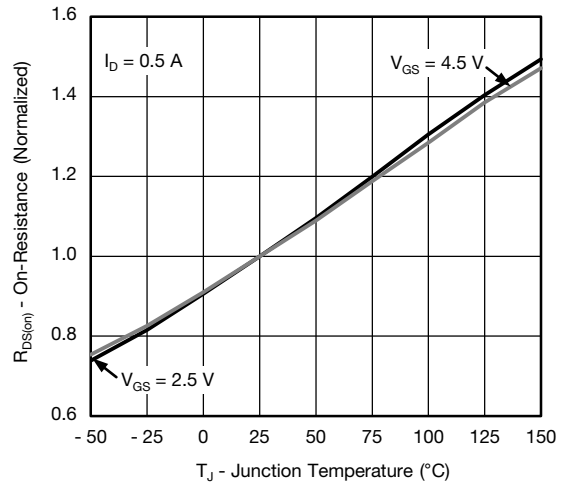


Capacitance

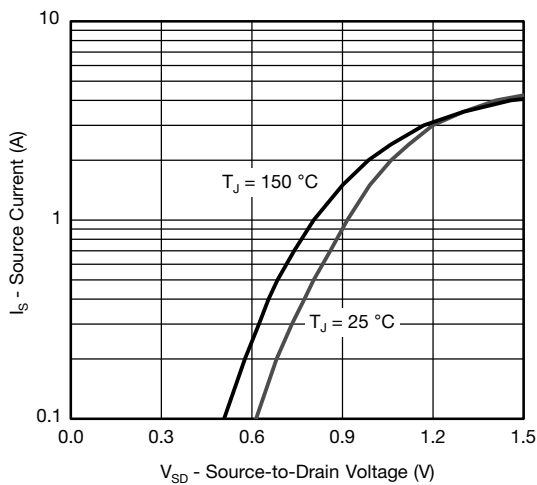
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



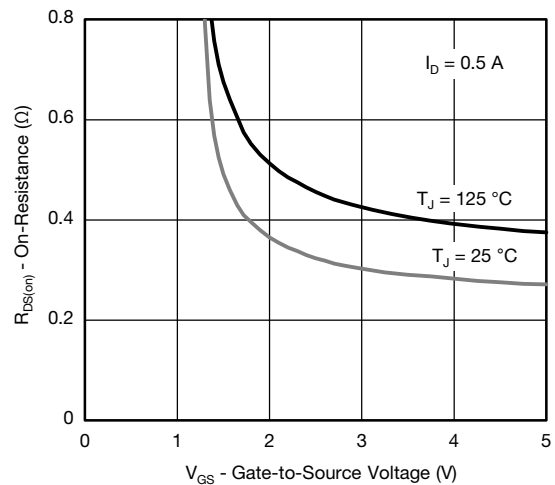
Gate Charge



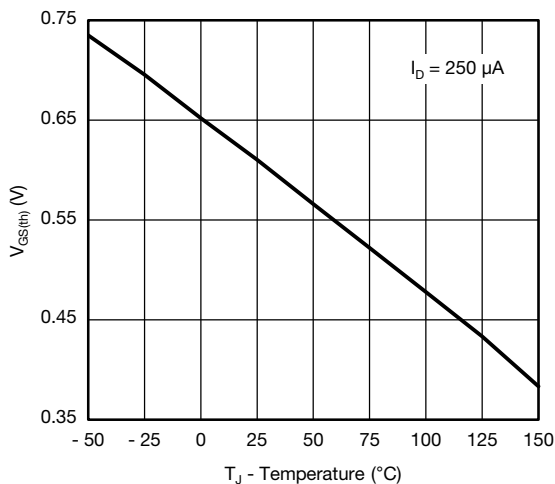
On-Resistance vs. Junction Temperature



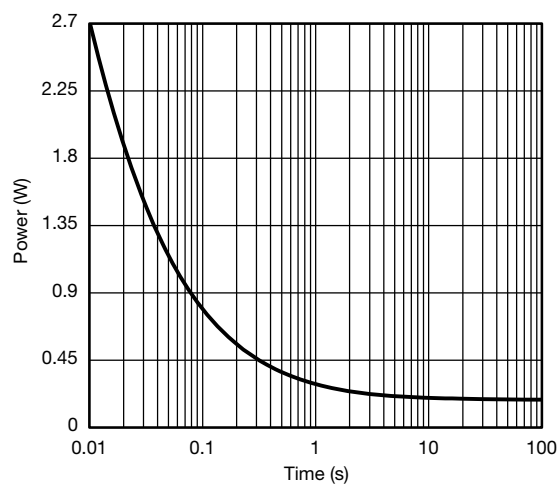
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



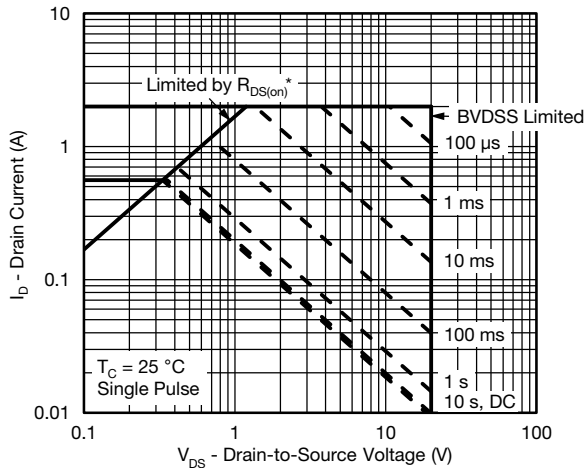
Threshold Voltage



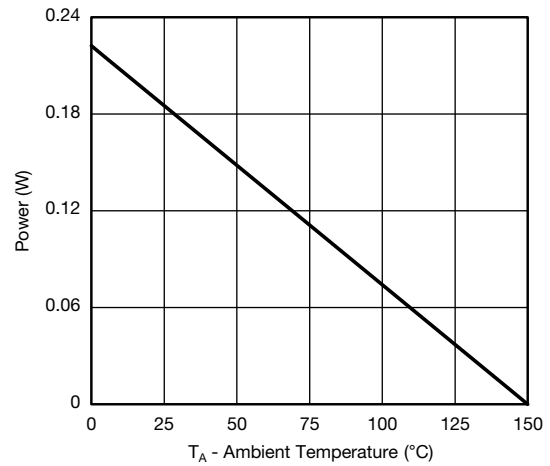
Single Pulse Power, Junction-to-Ambient



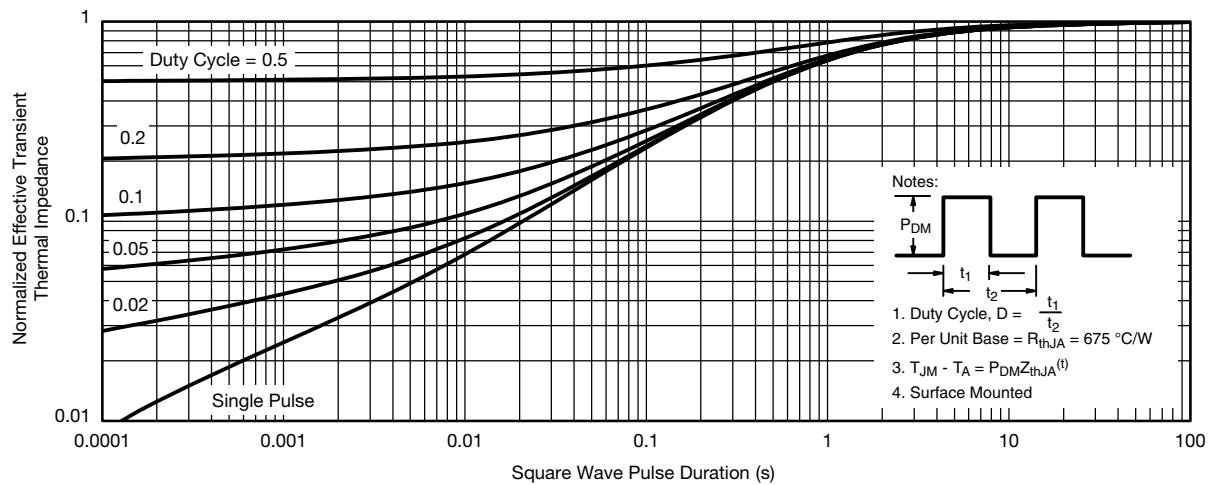
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient



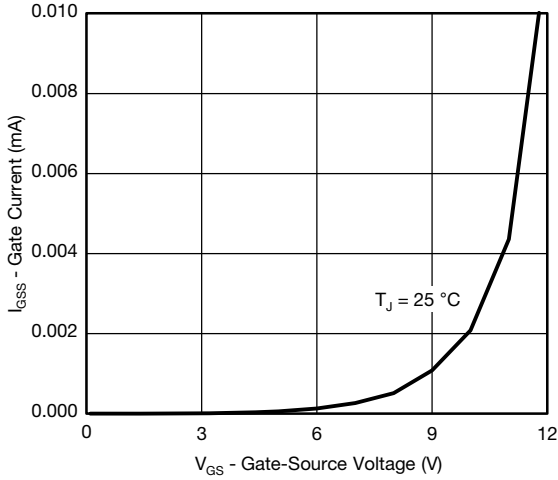
Power Derating, Junction-to-Ambient



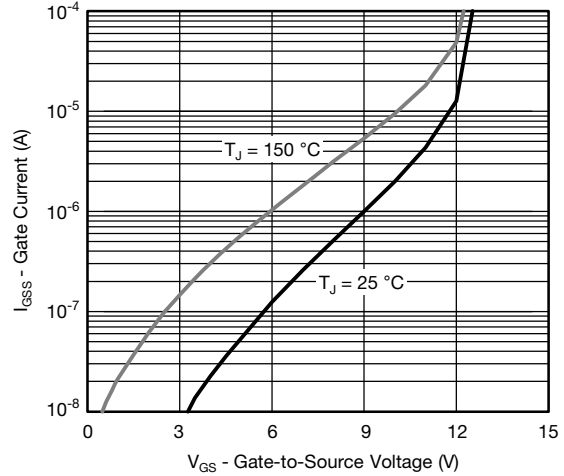
Normalized Thermal Transient Impedance, Junction-to-Ambient



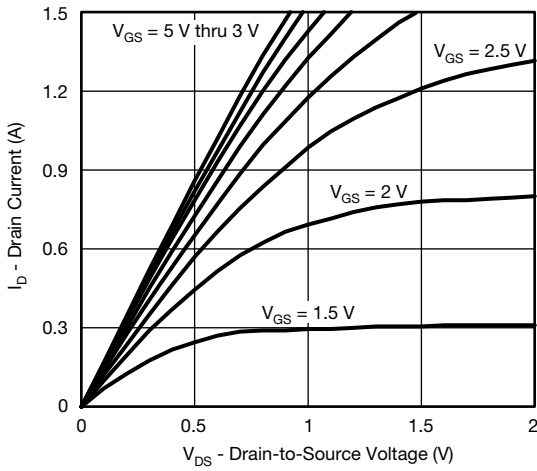
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



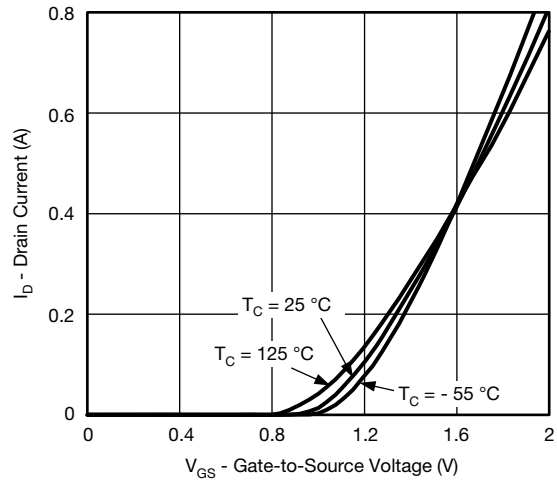
Gate Current vs. Gate-Source Voltage



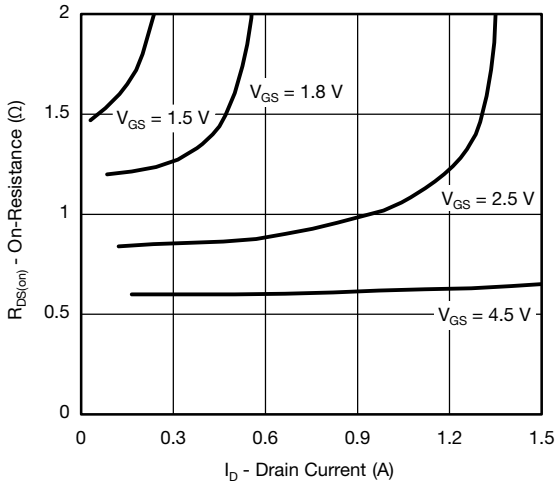
Gate Current vs. Gate-Source Voltage



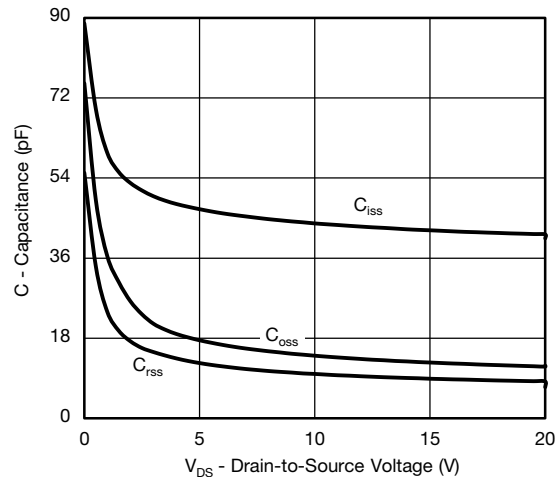
Output Characteristics



Transfer Characteristics



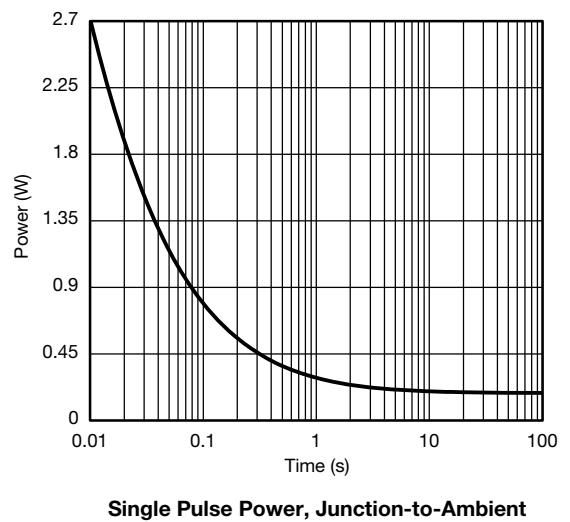
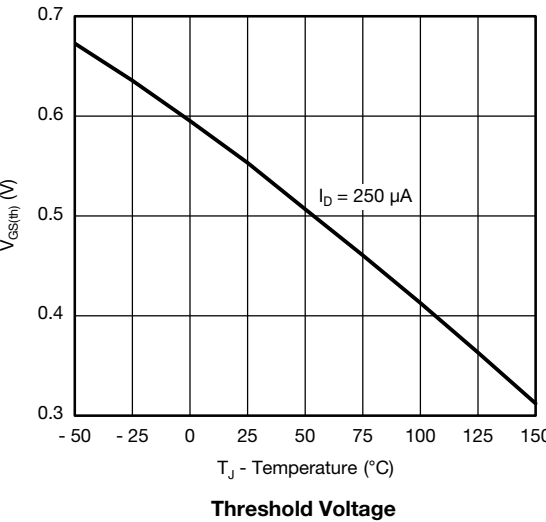
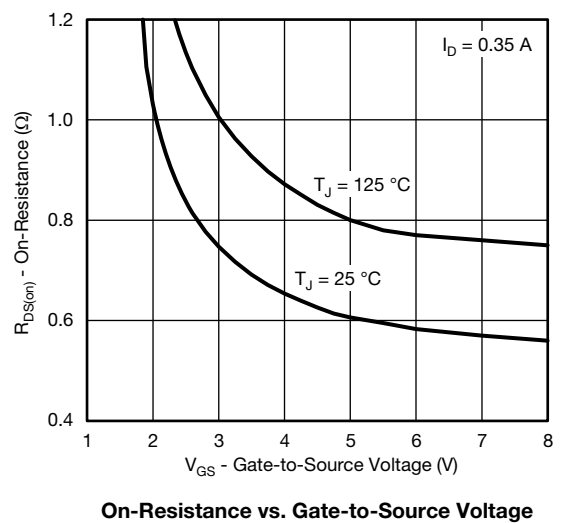
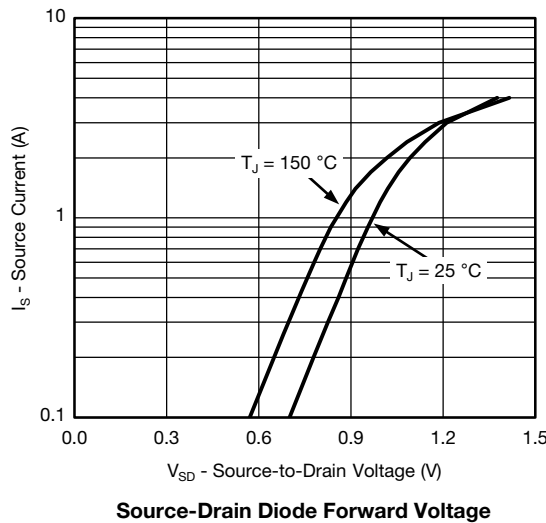
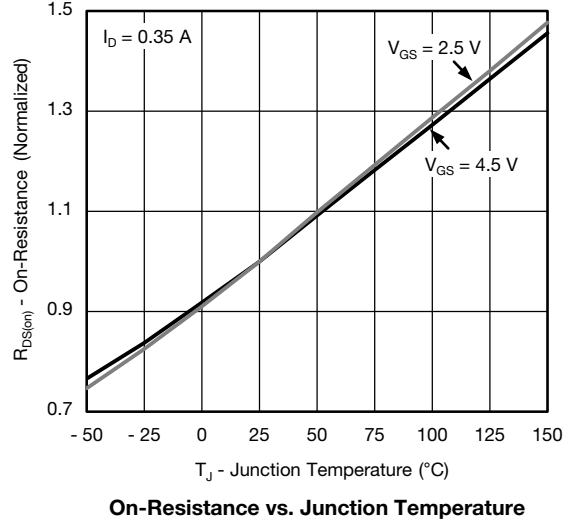
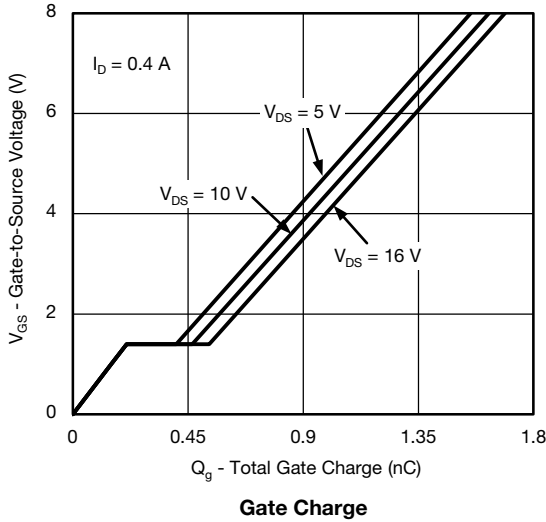
On-Resistance vs. Drain Current



Capacitance

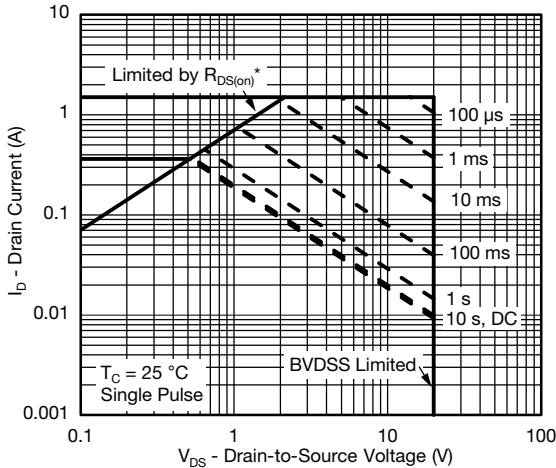


P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

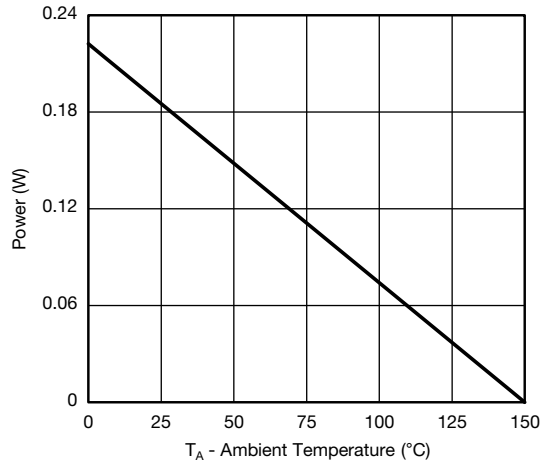




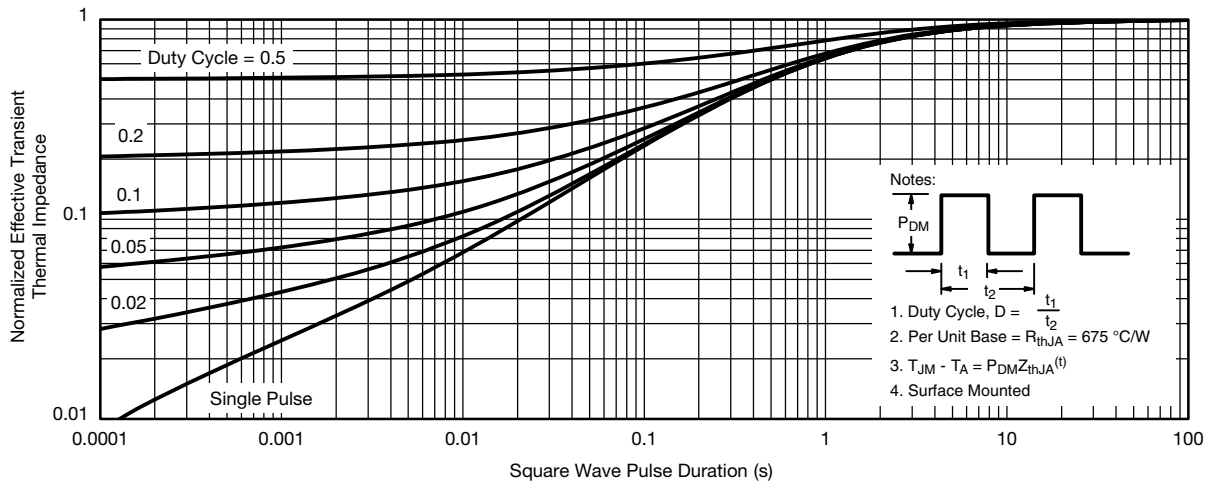
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient



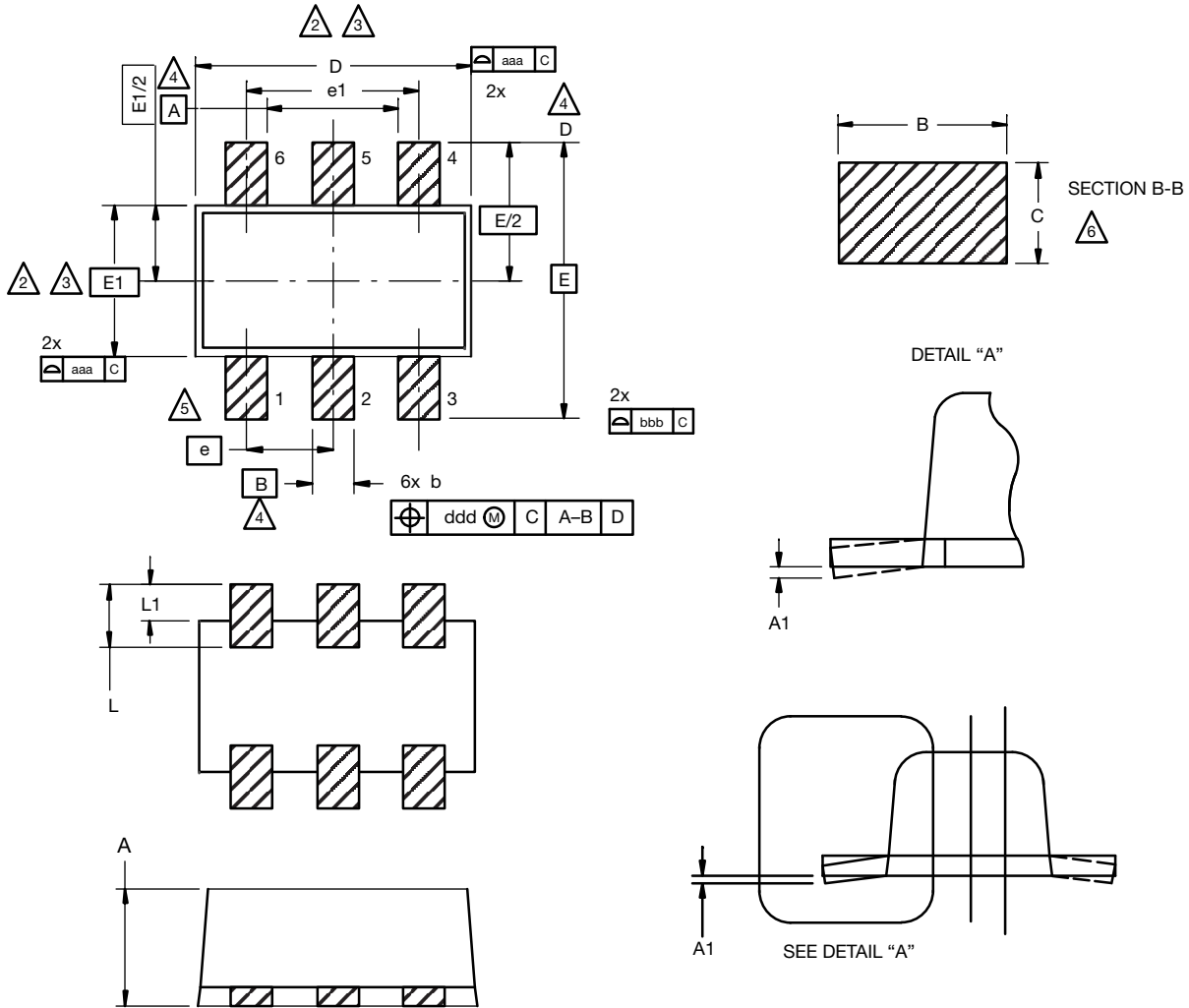
Power Derating, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267535.

SC-89 6-Leads (SOT-563F)



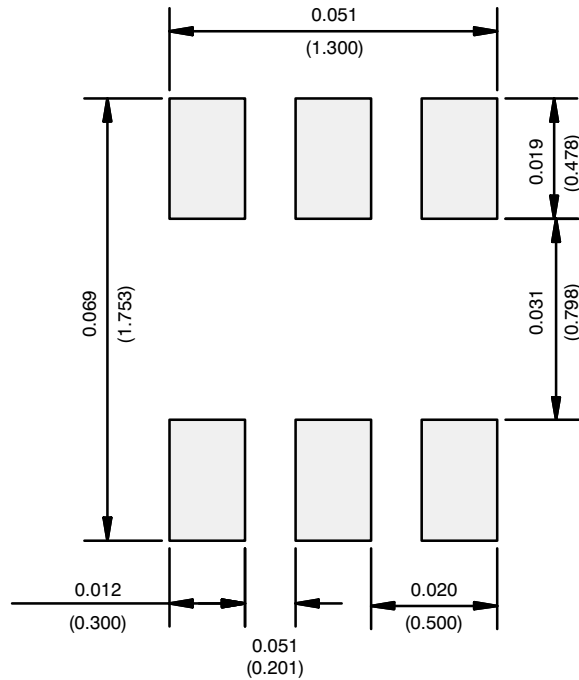
Notes

- 1. Dimensions in millimeters.
- ⚠ Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.
- ⚠ Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.
- ⚠ Datums A, B and D to be determined 0.10 mm from the lead tip.
- ⚠ Terminal numbers are shown for reference only.
- ⚠ These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

| DIM. | MILLIMETERS | | |
|------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.56 | 0.58 | 0.60 |
| A1 | 0 | 0.02 | 0.10 |
| b | 0.15 | 0.22 | 0.30 |
| c | 0.10 | 0.14 | 0.18 |
| D | 1.50 | 1.60 | 1.70 |
| E | 1.50 | 1.60 | 1.70 |
| E1 | 1.15 | 1.20 | 1.25 |
| e | 0.45 | 0.50 | 0.55 |
| e1 | 0.95 | 1.00 | 1.05 |
| L | 0.25 | 0.35 | 0.50 |
| L1 | 0.10 | 0.20 | 0.30 |

C14-0439-Rev. C, 11-Aug-14
DWG: 5880

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.